

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11	("4168990" "4169740" "4199773" "4463492" "4775641" "5064775" "5244820" "5403762" "5501989" "5532175" "5565690").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L2	9	L1 and oxide	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L3	7	L1 and oxide and crystal\$6	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L4	150	crystal\$6 with lattice with anneal\$6 with repair\$3	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L5	110	L4 and gate	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:50
L6	14	L5 and oxide with mask with implant\$6	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L7	21	crystalline with repair with lattice	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L8	26	crystalline with repair\$3 with lattice	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L9	30	crystalline with repair\$3 with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 22:55

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L10	0	L9 and ((impurit\$3 or dop\$3) with mask with oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L11	0	polycrystalline with repair\$3 with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L12	0	polycrystal\$4 with repair\$3 with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L13	1132	crystal\$6 with anneal\$4 with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L14	171	crystal\$6 with anneal\$4 with lattice same repair\$3	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L15	11	L14 and ((impurit\$3 or dop\$3) with mask with oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49

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L16	34	L14 and (mask with oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L17	0	laser with lattice with repair\$3 same (polysilicon or crystalline) and oxide with mask with boron	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L18	3249	laser with recrystal\$6 (polysilicon or crystalline) and oxide with mask with boron	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L19	6	laser with recrystal\$6 with (polysilicon or crystalline) and oxide with mask with boron	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L20	16	"4648909"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L21	1428	implant\$6 with boron with oxide with mask	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49

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L22	10	L21 and laser with recrystal\$6	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L23	14	L21 and laser with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L24	11	("4168990" "4169740" "4199773" "4463492" "4775641" "5064775" "5244820" "5403762" "5501989" "5532175" "5565690").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L25	0	L24 and peak with oxide	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L26	5366	peak with oxide	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L27	713	peak with concentration with oxide	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L28	406	L27 and crystal\$6	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L29	27	L27 and crystal\$6 with laser	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L30	103	L27 and crystal\$6 with anneal\$3	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L31	16	L27 and crystal\$6 with anneal\$3 same lattice	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49

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L32	36	L27 and anneal\$3 same lattice	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L33	108	"5292675"	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L34	1659	oxide with mask with boron	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L35	1200	L34 and gate	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L36	162	oxide with mask with boron and lattice and gate	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L37	5	thick adj oxide with mask with boron-and lattice and gate	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L38	64	"6011277"	US-PGPU B; USPAT; USOCR	OR	OFF	2007/10/25 22:49
L39	21	"5889315" and polysilicon	US-PGPU B; USPAT; USOCR	OR	ON	2007/10/25 22:49
L40	10616	L1 L2 L3 L4 L5 L6 L7 L8 L9 L10 L11 L12 L13 L14 L15 L16 L17 L18 L19 L20 L21 L22 L23 L24 L25 L26 L27 L28 L29 L30 L31 L32 L33 L34 L35 L36 L37 L38 L39	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:49
L41	5	9 and insulat\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:54

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L42	0	41 and peak adj concentration	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 22:54
L43	0	crystalline with repair\$3 with lattice and peak adj concentration	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 23:08
L44	11	"6353244"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 23:08
L45	115	438/181.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 23:08
L46	1739	438/151.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 23:08
L47	1318	438/166.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 23:08

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L48	7	crystal\$4 with repair\$3 with lattice and peak adj concentration	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 23:11
L49	0	45 and crystal\$4 with repair\$3 with lattice and peak adj concentration	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 23:11
L50	0	46 and crystal\$4 with repair\$3 with lattice and peak adj concentration	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 23:11
L51	0	47 and crystal\$4 with repair\$3 with lattice and peak adj concentration	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/10/25 23:11
S1	47	("20020094008" "20030022471" "20040069751" "20040119955" "20040169023" "20040171237" "20040259387" "5643801" "5643826" "5897799" "5900980" "5923962" "5953597" "5959779" "6002523" "6038075" "6156997" "6242292" "6528397" "6544825" "6548370" "6700096" "6806498").PN.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 16:57
S2	12	S1 and absorption adj coefficient	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 16:57

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S3	12	S2 and puls\$3	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 16:57
S4	8	S3 and second adj laser	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 18:28
S5	5	S4 and harmonic	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 18:35
S6	1368	memory adj cell and column adj direction and cell adj column	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 18:36
S7	8	S6 and lower adj inter adj electrode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 18:45
S8	235960	Tanaka.in.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 18:44

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S9	55405	Arai.in.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 18:45
S10	7	S8 and lower adj inter adj electrode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 18:45
S11	7	S9 and lower adj inter adj electrode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 18:45
S12	18	control adj (layer or film) with oxide same dopant	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 20:54
S13	1468	control\$6 with oxide same dopant	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 20:54
S14	131	control\$6 with oxide with dopant with concentration	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 20:59

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S15	30	"6165876"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 20:59
S16	11	("4168990" "4169740" "4199773" "4463492" "4775641" "5064775" "5244820" "5403762" "5501989" "5532175" "5565690").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 21:03
S17	9	S16 and oxide	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 21:03
S18	7	S16 and oxide and crystal\$6	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 21:25
S19	135	crystal\$6 with lattice with anneal\$6 with repair\$3	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 21:25
S20	98	S19 and gate	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 21:25
S21	12	S20 and oxide with mask with implant\$6	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 21:41
S22	21	crystalline with repair with lattice	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 21:41
S23	25	crystalline with repair\$3 with lattice	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 21:41
S24	29	crystalline with repair\$3 with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:42

EAST Search History

S25	0	S24 and ((impurit\$3 or dop\$3) with mask with oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:44
S26	0	polycrystalline with repair\$3 with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:42
S27	0	polycrystal\$4 with repair\$3 with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:43
S28	978	crystal\$6 with anneal\$4 with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:43
S29	154	crystal\$6 with anneal\$4 with lattice same repair\$3	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:43
S30	8	S29 and ((impurit\$3 or dop\$3) with mask with oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:45

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S31	28	S29 and (mask with oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:53
S32	0	laser with lattice with repair\$3 same (polysilicon or crystalline) and oxide with mask with boron	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:54
S33	2902	laser with recrystal\$6 (polysilicon or crystalline) and oxide with mask with boron	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 21:54
S34	5	laser with recrystal\$6 with (polysilicon or crystalline) and oxide with mask with boron	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 22:08
S35	16	"4648909"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 22:19
S36	1323	implant\$6 with boron with oxide with mask	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 22:19

EAST Search History

S37	8	S36 and laser with recrystal\$6	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 22:19
S38	9	S36 and laser with lattice	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/25 22:19
S39	11	("4168990" "4169740" "4199773" "4463492" "4775641" "5064775" "5244820" "5403762" "5501989" "5532175" "5565690").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 22:31
S40	0	S39 and peak with oxide	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 22:31
S41	4632	peak with oxide	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 22:31
S42	604	peak with concentration with oxide	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 22:32
S43	333	S42 and crystal\$6	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 22:32
S44	13	S42 and crystal\$6 with laser	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 22:33
S45	86	S42 and crystal\$6 with anneal\$3	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 22:33
S46	14	S42 and crystal\$6 with anneal\$3 same lattice	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 22:33

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S47	32	S42 and anneal\$3 same lattice	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 23:15
S48	90	"5292675"	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 23:20
S49	1528	oxide with mask with boron	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 23:22
S50	1102	S49 and gate	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 23:21
S51	150	oxide with mask with boron and lattice and gate	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 23:23
S52	5	thick adj oxide with mask with boron and lattice and gate	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/25 23:27
S53	49	"6011277"	US-PGPU B; USPAT; USOCR	OR	OFF	2006/06/26 00:00
S54	10	"5889315" and polysilicon	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/26 00:01
S55	0	"5889315" and polycrystalline	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/26 00:03
S56	0	"5889315" and laser	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/26 00:03
S57	15	"5889315" anddiborane	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/26 00:03
S58	3	"5889315" and diborane	US-PGPU B; USPAT; USOCR	OR	ON	2006/06/26 00:03

EAST Search History

S59	82193	(wafer or substrate) with insulating same (semiconductor or silicon or germanium or "Si" or "Ge")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/12 14:41
S60	3329	S59 and alignment with (hole or opening or trench or via)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/12 14:42
S61	249	S59 and alignment adj mark with (hole or opening or trench or via)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/12 14:42
S62	37	S61 and bulk	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/12 14:40
S63	285	(bulk adj (wafer or substrate)) with insulating same (semiconductor or silicon or germanium or "Si" or "Ge")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/12 14:41
S64	35	S63 and alignment with (hole or opening or trench or via)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/12 14:42

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S65	0	S63 and alignment adj mark with (hole or opening or trench or via)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/07/12 14:42
S66	0	S63 and alignment adj mark	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/07/12 14:42